

Open the Black Box of Memory

Content

Open the Black Box of Memory Overview



- Goal: Provide detailed view for design, layout and test engineers working with DRAM
- Duration: 2 to 3 days (dependent on seminar format)
- The focus is on (LP)DDR4/5 based on the changes from previous generations. This allows an easy transition for engineers knowing DDR3 to DDR4/5 and LPDDR4/5 memory.
- High level of detail for many topics, On the fly selection of topics that should be discussed more intensively
 - If a very close insight into some special features is required, please contact EyeKnowHow directly

Open the black Box of Memory Agenda part 1



- Seminar target and overview
- 2. Different applications and memories
- 3. DRAM basics
- 4. Evolution of commodity DRAM generations
- 5. Memory system performance
- 6. (LP)DDR4/5 spec: input timings
- 7. DDR3/4 spec: setup / hold derating
- IDD current definition
- 9. Different DIMM types and physical implementation
- 10. Setup for flexible module density

Open the black Box of Memory Agenda part 2



- 1. Error correction
- 2. Layout guidelines / DFT
- 3. Measurement and equipment
- 4. TDR measurement
- 5. Failure analysis
- 6. Transient simulation
- 7. PDN simulation
- 8. S-Parameters
- 9. Rules of thumb and some theory

Open the black Box of Memory Agenda part 3



- 1. Overview on training options
- 2. Power up sequence and "low speed signaling"
- 3. ZQ calibration
- 4. CA bus calibration (per CA bus or per bit)
- Write leveling
- 6. Write DQS / DQ timing alignment (per byte or per bit)
- 7. Receive enable training via MPR
- 8. Read DQS / DQ timing alignment (per byte or per bit)
- 9. DDR4 VrefDQ training
- 10. Conclusion